

1. Radiation Hardness Studies of thin and low bulk resistivity LGADs, Geetika Jain, Chakresh Jain, Saumya, Namrata Agrawal, Ashutosh Bhardwaj and Kirti Ranjan, *Semiconductor Science and Technology*, 36(2021), 065016.
2. Modeling of neutron radiation-induced defects in silicon particle detectors, Chakresh Jain, Saumya Saumya, Geetika Jain, Ranjeet Dalal, Namrata Agrawal, Ashutosh Bhardwaj and Kirti Ranjan, *Semicond. Sci. Technol.* 35 (2020) 045021.
3. TCAD silicon device simulation for high level of radiation damage, N. Agrawal, K. Androsov, A. Bhardwaj, M.A. Ciocci, M.T. Grippo, C. Jain, A. Kumar, A. Messineo, S. Parolia, K. Ranjan, S. Saumya, A. Sisodia and S. Sondh, *JINST* 15 (2020) C05066.
4. High-voltage planar Si detectors for high-energy physics experiments: comparison between metal-overhang and field-limiting ring techniques, K. Ranjan, A. Bhardwaj, Namrata, S. Chatterji, A. K. Srivastava, Ashish Kumar, Manoj Kumar Jha and R. K. Shivpuri, *Solid State Electronics* 48, (2004)1587.
5. Simulation Study of irradiated Si sensors equipped with metal-overhang for applications in LHC environment, S. Chatterji, A. Bhardwaj, K. Ranjan, Namrata, A.K. Srivastava, Ashish Kumar, Manoj Kumar Jha, S.L.Khanna and R. K. Shivpuri, *IEEE Trans. Nucl. Sci* 51(2), (2004) 298.
6. Breakdown voltage analysis of neutron irradiated silicon detectors, A. Bhardwaj, K. Ranjan, Namrata, S. Chatterji, A. K. Srivastava, A. Kumar, M. K. Jha and R. K. Shivpuri, *Eur. Phys. J. AP.* 24, (2003)171.
7. Analysis of interstrip capacitance of Si microstrip detector using simulation approach, S. Chatterji, A. Bhardwaj, K. Ranjan, Namrata, A. K. Srivastava and R. K. Shivpuri, *Solid State Electronics* 47, (2003)1491.
8. Comparison of p⁺n junction Formed by BF₂⁺ and Boron Implantation in Silicon Microstrip Detector with Low and High Thermal Budget: Impact of Fluorine on Electrical Characteristics, Ajay K. Srivastava, A. Bhardwaj, K. Ranjan, Namrata, S. Chatterji, and R. K. Shivpuri, *Material Science in Semiconductor Processing* Vol.6, Issues 5-6, (2003)555.
9. A CAD investigation of Metal-overhang on multiple guard ring design for high voltage operation of Si sensors, A. Bhardwaj, K. Ranjan, Namrata, S. Chatterji, A. K. Srivastava and R. K. Shivpuri, *Semicond. Sci. Technol.* 17, (2002)1226.

10. Performance characteristics of semi-insulator and dielectric passivated Si strip detectors, K. Ranjan, A. Bhardwaj, Namrata, S. Chatterji, A. K. Srivastava and R. K. Shivpuri, *Physica Status Solidi (a)* 191(2), (2002)658.
11. Analysis and Comparison of the breakdown performance of Semi-insulator and dielectric passivated Si Strip detectors, K. Ranjan, A. Bhardwaj, Namrata, S. Chatterji, A. K. Srivastava and R. K. Shivpuri, *Nuclear Instruments and Methods in Physical Research A* 495, (2002)191.
12. Charged particle multiplicity distributions in different rapidity windows in 800 GeV proton-nucleus interactions, Namrata, A. Bhardwaj K. Ranjan, S. Chatterji, A. K. Srivastava, A. Kumar, M. K. Jha and R. K. Shivpuri, *Eur. Phys. Journal A* 13, (2002)405.
13. Two Dimensional Breakdown Voltage Analysis and Optimal Design of Silicon Microstrip Detector Passivated by Dielectric, A. K. Srivastava, A. Bhardwaj, Namrata, S. Chatterji, A. K. Srivastava and R. K. Shivpuri, *Semicond. Sci. Technol.* 17, (2002)427.
14. Annealing behaviour of boron implanted defects in Si detector: impact on breakdown performance, S. Chatterji, K. Ranjan, A. Bhardwaj, Namrata, A. K. Srivastava and R. K. Shivpuri, *Eur. Phys. J. AP* 17, (2002) 223.
15. A new approach to the optimal design of multiple field-limiting ring structures, A. Bharadwaj, K. Ranjan, Namrata, S. Chatterji, A. K. Srivastava and R. K. Shivpuri, *Semicond. Sci. Technol.* 16, (2001)849.
16. Analysis and Optimal Design of Si Microstrip Detector with Overhanging Metal Electrode, K. Ranjan, A. Bhardwaj, Namrata, S. Chatterji, A. K. Srivastava and R. K. Shivpuri, *Semicond. Sci. Technol.* 16, (2001)635.
17. Rapidity Correlation in 800 GeV proton-nucleus interactions, Namrata, A. Bhardwaj K. Ranjan, S. Chatterji, A. K. Srivastava, A. Kumar, M. K. Jha and R. K. Shivpuri, *Eur. Phys. Journal A* 12, (2001)9.